Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO263 (D2PAK) surface mountable plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{i(max)} = 150$ °C).

2. Features and benefits

- · High bidirectional blocking voltage capability
- · High junction operating temperature capability
- · High thermal cycling performance
- · Planar passivated for voltage ruggedness and reliability
- · Surface mountable package
- · Very high current surge capability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- · Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit		
V_{RRM}	repetitive peak reverse voltage		600			V		
I _{T(AV)}	average on-state current	half sine wave;T _{mb} ≤ 129 °C; <u>Fig 1</u>	12.7			А		
I _{T(RMS)}	RMS on-state current	half sine wave;T _{mb} ≤ 129 °C; Fig 2; Fig 3	20			А		
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig 4; Fig 5	210			А		
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$	231		Α			
T _j	junction temperature		150		°C			
Symbol	Parameter	Conditions	Min Typ		Max	Unit		
Static cha	Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1\text{A; } T_j = 25 \text{ °C;} $ Fig 7	- 4.5 32		mA			
Dynamic o	Dynamic characteristics							

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV _D /dt	rate of rise of off-state	V_{DM} = 402 V; T_j = 150 °C; exponential	1000	-	-	V/µs
	voltage	waveform; gate open circuit				

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode		A → K
3	G	gate		G sym037
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

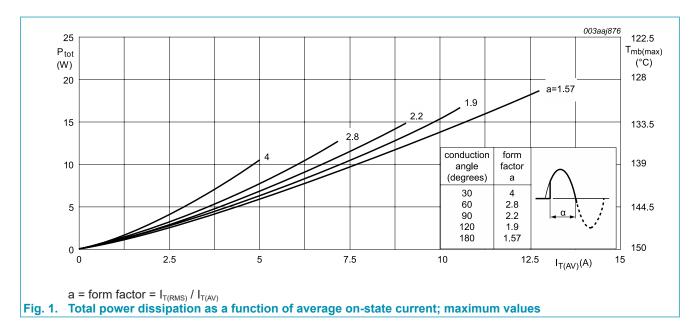
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Type number	Package	Orderable part number	Packing	Small packing	Package	Package
	Name		method	quantity	version	issue date
TYN20B-600T	TO263	TYN20B-600TJ	Reel	800	TO263E	26-May-2017

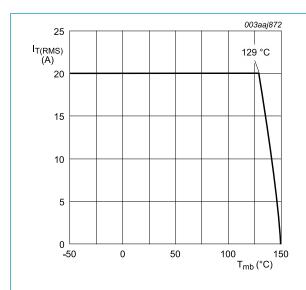
7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
V_{RRM}	repetitive peak reverse voltage		600	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig 1</u>	12.7	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig 2</u> ; <u>Fig 3</u>	20	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig 4; Fig 5	210	Α
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$	231	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	220.5	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 70 mA	100	A/µs
I _{GM}	peak gate current		5	А
V_{RGM}	peak reverse gate voltage		5	V
P_{GM}	peak gate power		20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	1	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C





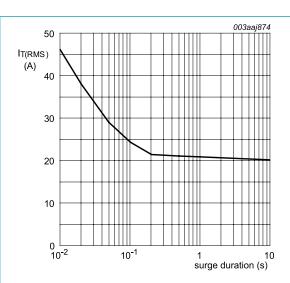


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

f = 50 Hz; T_{mb} =129 °C

Fig. 3. RMS on-state current as a function of surge duration; maximum values

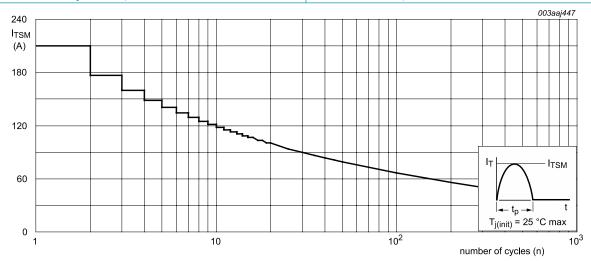
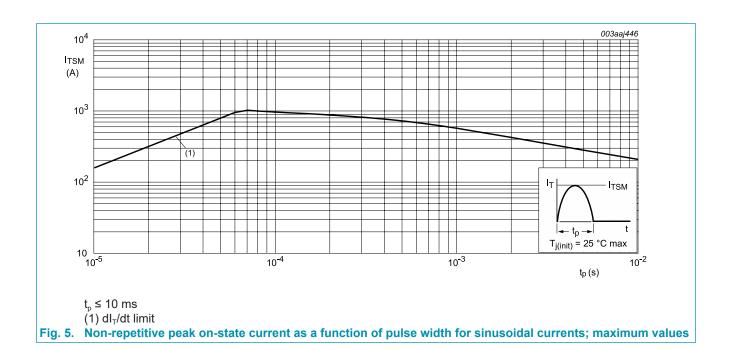


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	1.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	minimum footprint, FR4 board	-	55	-	K/W

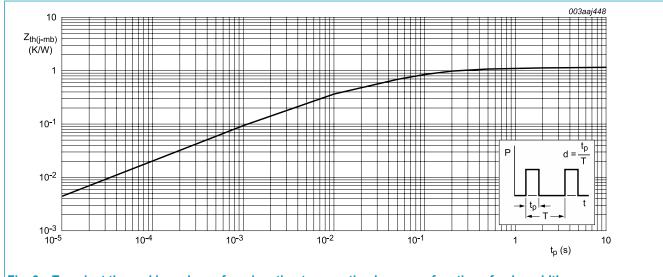


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		-	4.5	32	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$		-	21	60	mA
I _H	holding current	V _D = 12 V;T _j = 25 °C; <u>Fig. 9</u>		-	16	40	mA
V _T	on-state voltage	I _T = 32 A; T _j = 25 °C; <u>Fig. 10</u>		-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	0.7	1.3	V
		$V_D = 400V; I_T = 0.1 A; T_j = 150 °C$		0.2	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C		-	0.2	1	mA
I _R	reverse current	V _R = 600 V; T _j = 150 °C		-	0.2	1	mA
Dynamic	Dynamic characteristics						
dV_D/dt rate of rise of off-state voltage		V _{DM} = 402 V; T _j = 150 °C; exponential waveform; gate open circuit		1000	-	-	V/µs

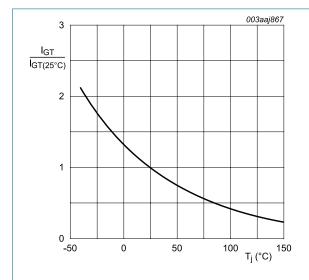


Fig. 7. Normalized gate trigger current as a function of junction temperature

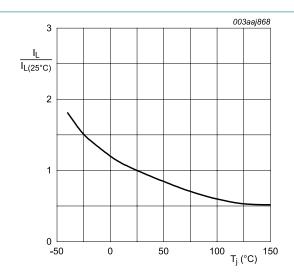
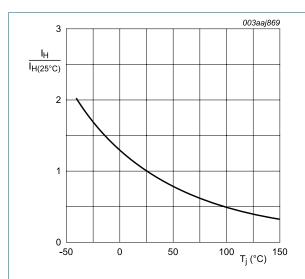
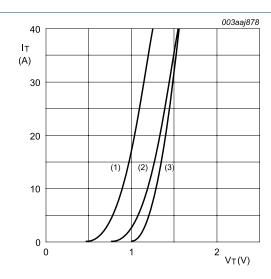


Fig. 8. Normalized latching current as a function of junction temperature





 V_o = 1.0485 V; R_s = 0.0133 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 9. Normalized holding current as a function of junction temperature

Fig. 10. On-state current as a function of on-state voltage

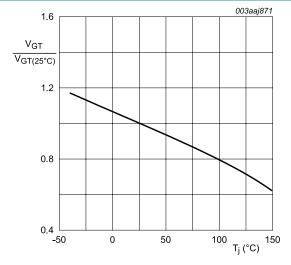
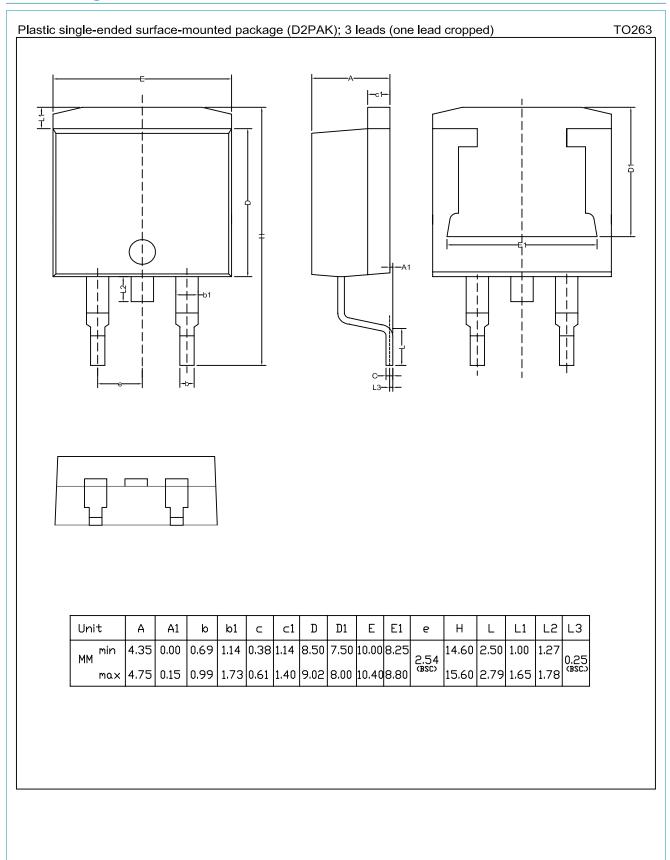


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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